

## 60V, 3A Low IQ Synchronous Buck Converter

### FEATURES

- Up to 95% Efficiency
- Input Voltage Range: 4.5V to 60V
- Output Voltage Range: 0.8V to 40V
- Continuous Output Current: 3A
- Adjustable switching frequency range: 250KHz to 1.2MHz
- Reference Voltage: 0.8V  $\pm 2\%$  @25°C
- Maximum Duty Cycle: 98%
- Integrated high-side MOSFET: 160mΩ
- Low Quiescent Current: 150μA
- Low Shutdown Current: 10μA
- Optional Operation Modes at Light-Load
- Over Current Protection
- Short Protection with Hiccup-Mode
- Internal Soft Startup
- Thermal Shutdown Protection
- Constant-On-Time Control scheme

### DESCRIPTIONS

The DP31263A is a low EMI signature, Asynchronous, step-down, COT mode converter with internal High-Side power MOSFETs. It offers a very compact solution to provide 3A continuous current over a wide input supply range, with excellent load and line regulation. DP31263A achieves low EMI signature with well controlled switching edges. Fault condition protection includes programmable -output over-voltage protection, and thermal shutdown. package.

Switching frequency is internally. Adjustable switching frequency range 250KHz to 1.2MHz, allowing the use of small surface mount inductors and capacitors. Low output voltages are easily supported with the 0.8V feedback reference voltage.

The DP31263A requires a minimal number of readily available, external components and is available in a ESOP8 package.

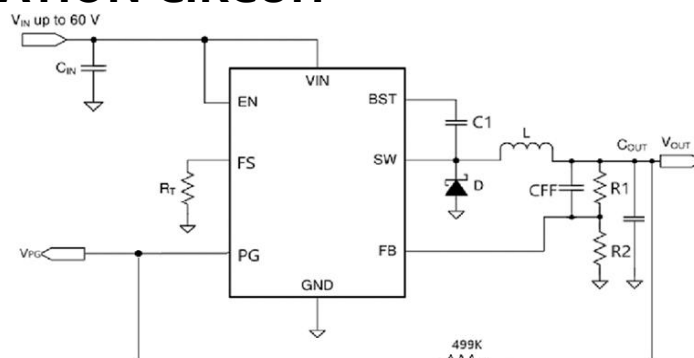
### APPLICATIONS

- POE
- Automotive Entertainment
- Wireless and DSL Modems
- Computer Entertainment
- Digital Still and Video Cameras
- GPS & E-Bike & E-motors

### ORDERING INFORMATION

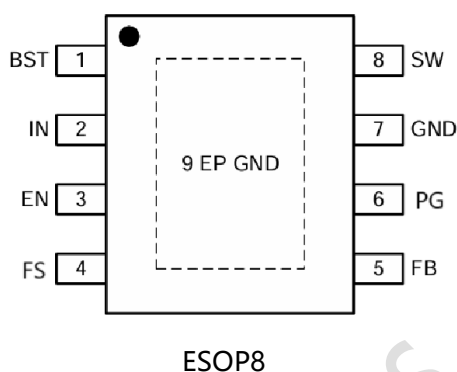
Part Number	Description
ESOP8	Pb free in T&R, 3000 Pcs/Reel

### TYPICAL APPLICATION CIRCUIT



## PRODUCT DESCRIPTION

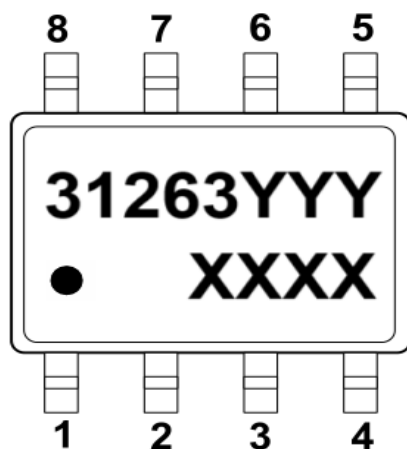
### ➤ Pin Arrangement



### ➤ Pin Configuration

ESOP8	Pin Name	Description
1	BST	Supply input for the high-side NFET gate drive circuit. Connect a 0.1 $\mu$ F capacitor between VBST and SW pins.
2	IN	Power supply voltage input
3	EN	Chip Enable Pin. Drive EN above 1.5V to turn on the part. Drive EN below 0.4V to turn it off. Do not leave EN floating
4	FS	Switching Frequency Set Pin.
5	FB	Feedback pin for the internal control loop. Connect this pin to an external feedback divider.
6	PG	Power Good Indication.
7	GND	Ground Pin
8	SW	Switch pin connected to the internal FET switches and inductor terminal. Connect the inductor of the output filter to this pin.
9	EP	Exposed Pad

## ➤ Marking Information



DP31263 for product name:

YYY refers to the following table description, represents different packaging and special functions

XXXX The first X represents the last year, 2020 is 0; The second X represents the month, in A-L 12 letters; The third and fourth X on behalf of the date, 01-31 said;

Marking	Model	Description
31263A	DP31263ASO	DP31263ASO Buck, 4.5V~60V, 3A, 500KHZ, VFB 0.8V, <b>DCM</b> , ESOP8

## ➤ Absolute Maximum Ratings

PARAMETER	Min	Max	Unit
VIN Voltage	-0.3	65	V
EN Voltage	-0.3	65	V
SW Voltage(DC)	-0.3	65	V
SW Voltage(AC less than 10ns while Switching)	-5	115	V
FB Voltage	-0.3	6.5	V
BS Voltage(vs SW)	-0.3	5	V
Operating junction temperature,TJ	-40	150	°C
Storage temperature, Tstg	-65	150	°C
Lead Temperature (Soldering, 10sec.)	-	260	°C

Over operating temperature range (unless otherwise noted)(1)

Note:(1)Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal

## ➤ Recommended Operating Conditions

PARAMETER	Min	Max	Unit
VIN Voltage(VIN)	4.5	60	V
VOUT Voltage(VIN)	0.8	40	V
Output current(Vout=5V)	0	3.5	A
Output current(Vout=12V)	0	3	A
TJ	-40	125	°C

Note : (1)All limits specified at room temperature (TA = 25°C) unless otherwise specified. All room temperature limits are 100% production tested. All limits at temperature extremes are ensured through correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

## ESD Ratings

PARAMETER	Description	Value	Unit
HBM	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
CDM	Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±200	V

Note : (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

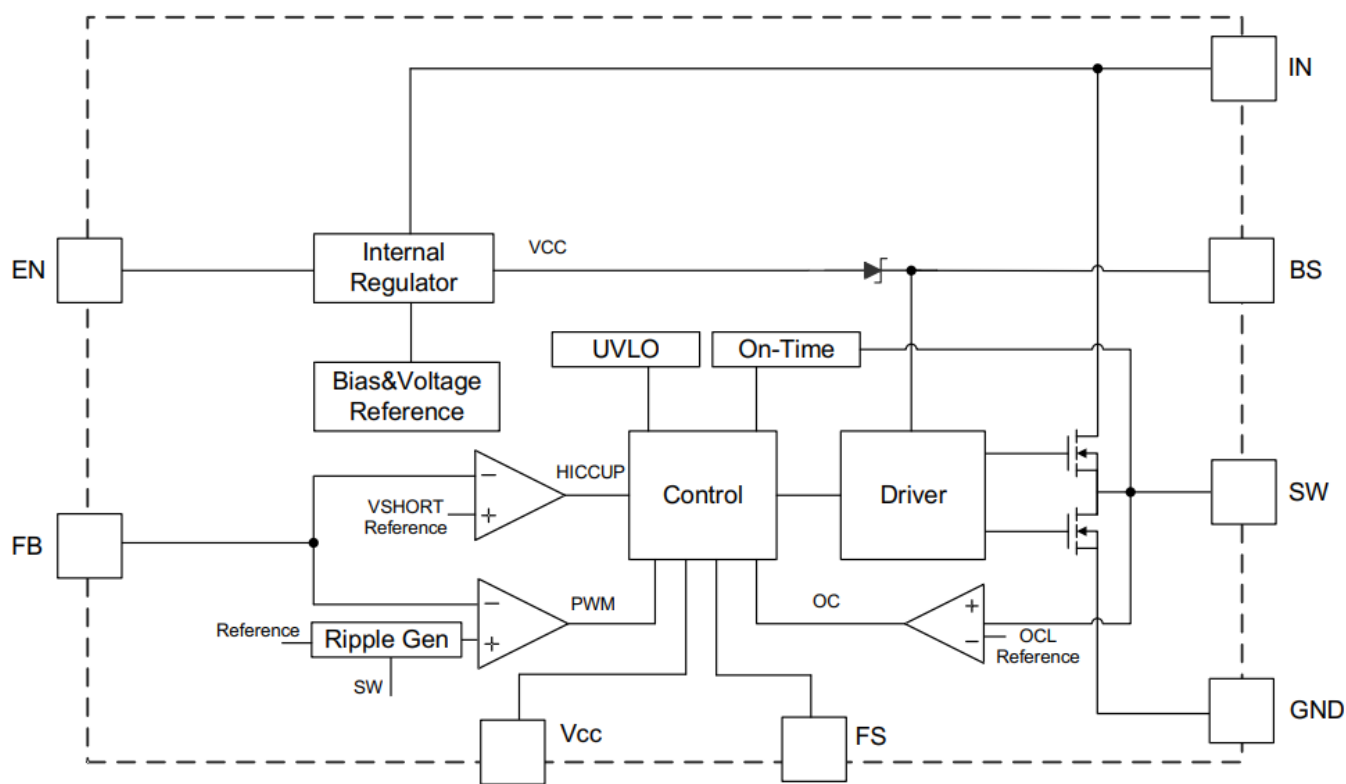
## ➤ Thermal Information

THERMAL METRIC	Description	ESOP8	Unit
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)(2)</sup>	48.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	52.4	°C/W
$R_{\theta JB}$	Junction-to-board(Bottom) thermal resistance	25.5	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	8.4	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	25.2	°C/W

Note (1): The package thermal impedance is calculated in accordance to JESD 51-7.

Note (2): Thermal Resistances were simulated on a 4-layer, JEDEC board

## BLOCK DIAGRAM



Block Diagram

**ELECTRICAL CHARACTERISTICS** (Typical at  $V_{IN}=12V$ ,  $T_J=25^{\circ}C$ , unless otherwise noted.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Input Voltage	$V_{IN}$		4		60	V
$V_{IN}$ Quiescent Current	$I_Q$	No-switching, $V_{EN}=12V$ , $V_{FB}=V_{REF}*105\%$ , $I_{out}=0A$		150		$\mu A$
Shutdown Current	$I_{SHDN}$	$V_{EN}=0V$		3		$\mu A$
$V_{IN}$ UVLO Rising Threshold	$V_{UVLO(R)}$	$V_{IN}$ Rising		4.2		V
$V_{IN}$ UVLO Falling Threshold	$V_{UVLO(F)}$	$V_{IN}$ Falling		3.9		V
$V_{IN}$ UVLO Hysteresis	$V_{UVLO(HYS)}$			0.3		V
FB Voltage	$V_{FB}$	$T_J=25^{\circ}C$	0.780	0.8	0.810	V
FB Leakage Current	$I_{FB(LKG)}$	$T_J=25^{\circ}C$	-100	10	100	nA
Switching Frequency	$F_{sw}$	FS Pin Float		250		KHZ
		FS=200K		500		KHZ
		FS=80K		1200		KHZ
Max duty cycle	$D_{max}$				98	%
Mini on Pulse Width	$T_{ON(MIN)}$			130		ns
High-Side Switch Current Limit	$I_{HS(OC)}$	$V_{IN}=48V$ , $V_{FB}=90\%$		3.5		A
High-Side MOS ON-Resistance	$R_{DS(ON)(HS)}$	$I_{sw}=100mA$		160		m $\Omega$
EN Rising Threshold	$V_{EN(R)}$	EN Rising	1.5			V
EN Falling Threshold	$V_{EN(F)}$	EN Falling			0.3	V
EN Hysteresis	$V_{EN(HYS)}$			0.2		V
Soft Start	$T_{SS}$	10%* $V_{out}$ to 90%* $V_{out}$		2		ms
Over-Temperature Protection	$T_{SD}$			160		$^{\circ}C$
Over-Temperature Protection hysteresis	$\Delta T_{SD}$			30		$^{\circ}C$

## TYPICAL CHARACTERISTICS

Test Condition:  $T_A = 25^\circ\text{C}$ ,  $V_{IN}=54\text{V}$ ,  $V_{out}=12\text{V}$ , unless otherwise noted.

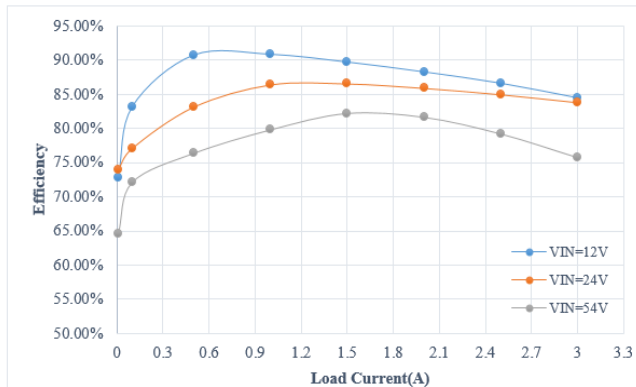


Figure1 5V Output Efficiency

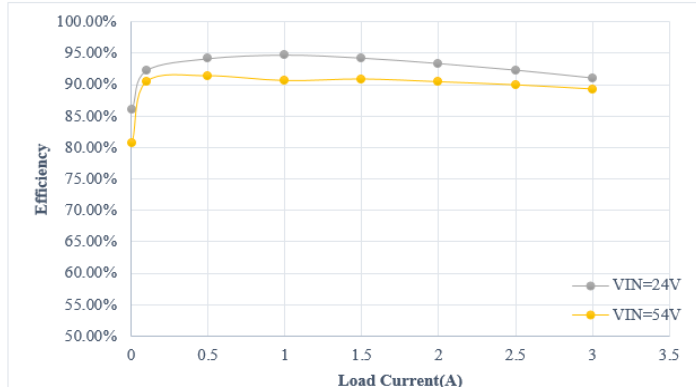


Figure2 12V Output Efficiency

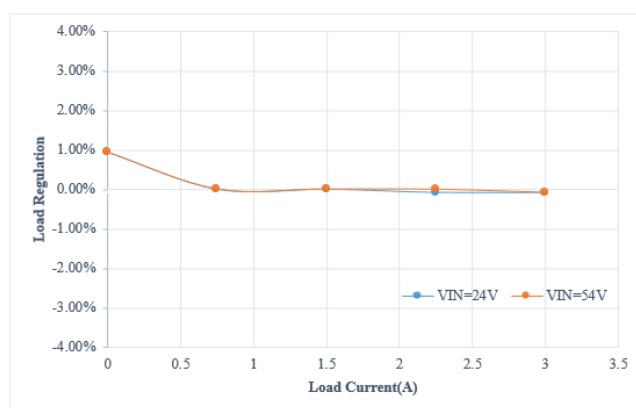


Figure3 12V Output Load Regulation

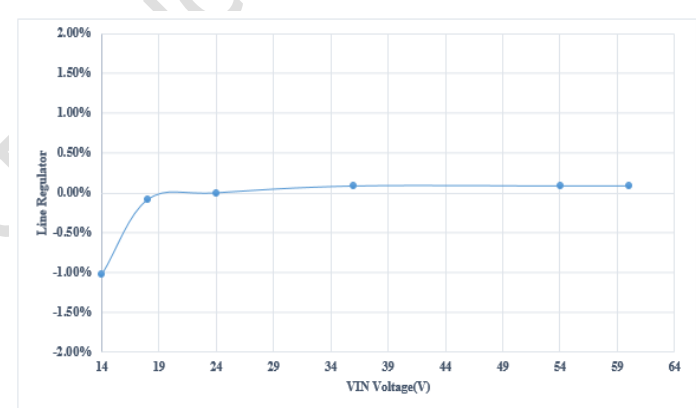
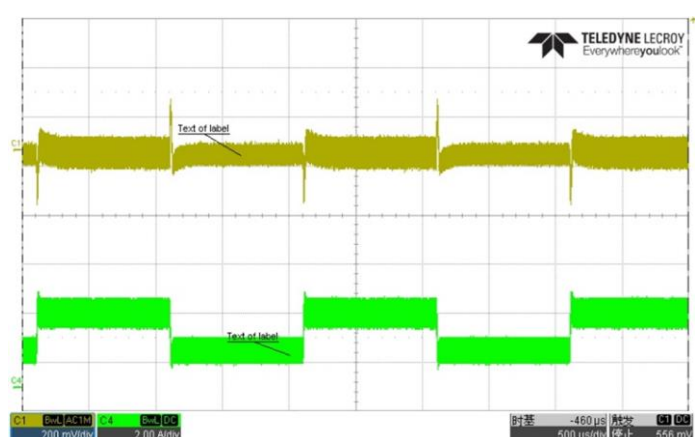


Figure4 Line Regulation  $I_{out}=3\text{A}$



Load Step 0.1 to 1.5A, 2A/us Slew rate

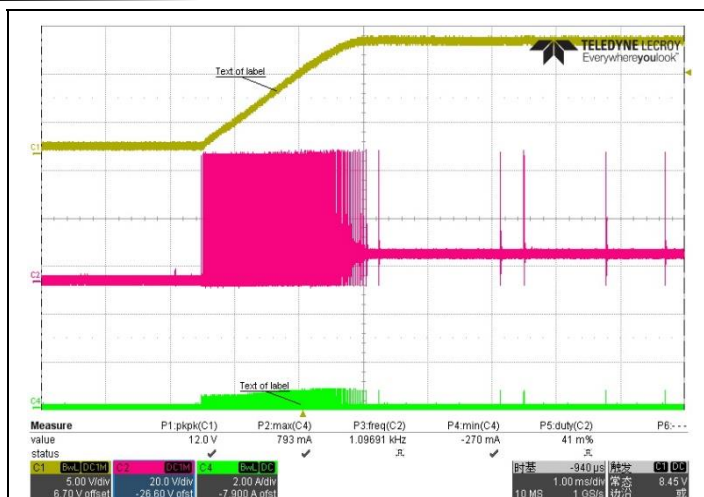
Figure5 Load Transient



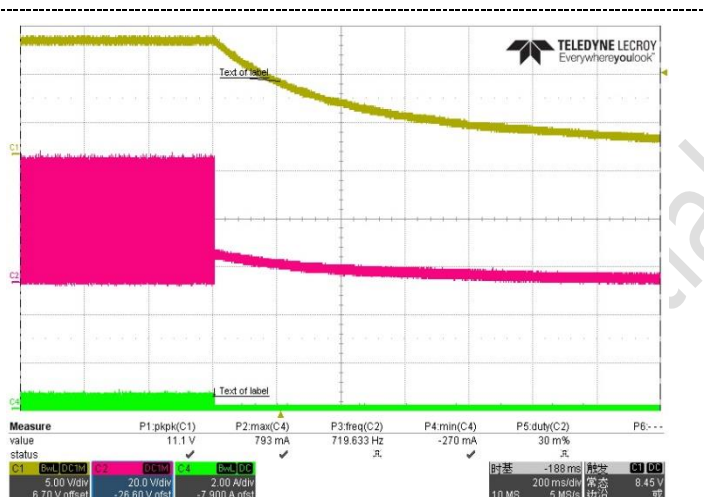
Load Step 1.5 to 3A, 2A/us Slew rate

Figure6 Load Transient

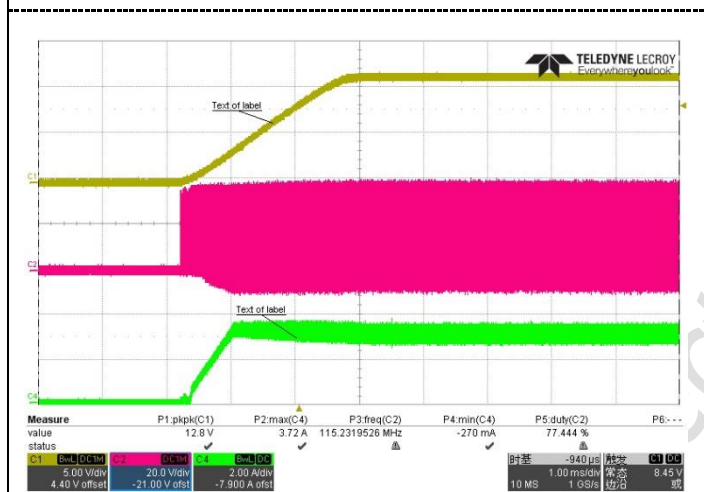




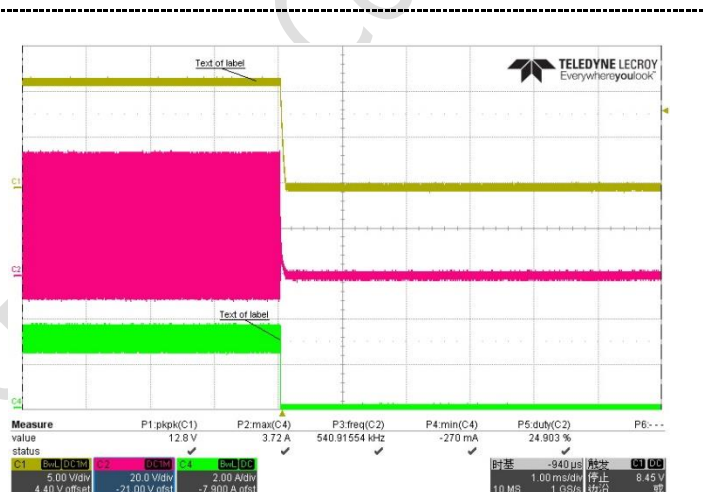
**Figure7 VIN StartUp with No Load**



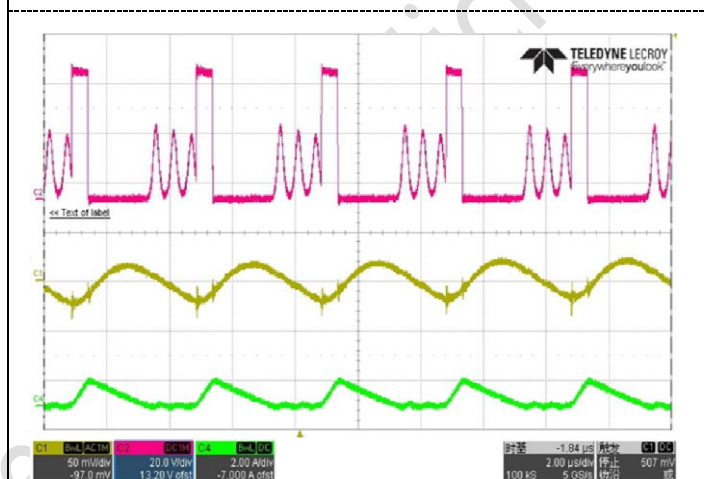
**Figure8 ShutDown with No Load**



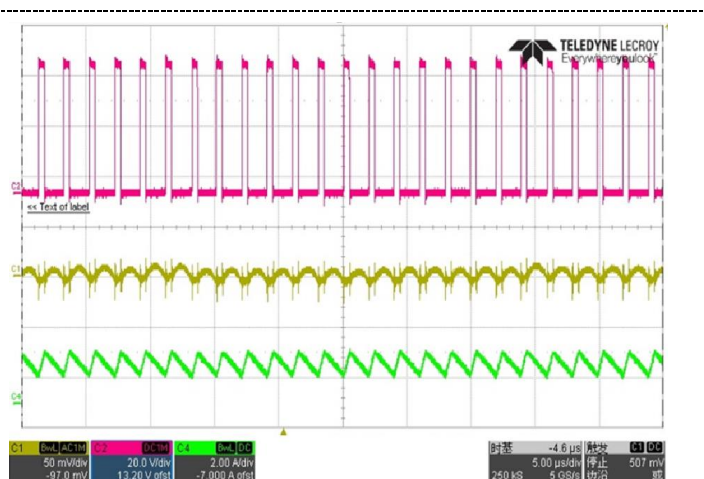
**Figure9 VIN StartUp with 3A Load**



**Figure10 VIN ShutDown with 3A Load**



**Figure11 DCM with Iout=0.1A**



**Figure12 CCM with Iout=3A**

## FUNCTIONS DESCRIPTION

### ● Feature Description

The DP31263A is a COT mode step down DC/DC converter that provides excellent transient response with no extra external compensation components. This device contains an internal, low resistance, high voltage power MOSFET, Switching frequency is internally. Adjustable switching frequency range 250KHz to 1.2MHz

### ● Thermal Shutdown

The internal thermal-shutdown circuitry forces the device to stop switching if the junction temperature exceeds 160 ° C typically. Once the junction temperature falls below the falling threshold, the device returns to normal operation automatically.

### ● Soft Start

The soft-start is implemented to prevent the converter output voltage from overshooting during startup. When the chip starts, the internal circuitry generates a soft-start voltage (SS) ramping up from 0V to 0.8V. When it is lower than the internal reference (REF), SS overrides REF so the error amplifier uses SS as the reference. When SS is higher than REF, REF regains control. The SS time is internally max to 3ms.

### ● UNDER-VOLTAGE LOCKOUT (UVLO)

Under-voltage lockout (UVLO) protects the chip from operating at an insufficient supply voltage. UVLO protection monitors the internal regulator voltage. When the voltage is lower than UVLO threshold voltage, the device is shut off. When the voltage is higher than UVLO threshold voltage, the device is enabled again.

### ● Startup AND Shutdown

The If both VIN and EN are higher than their

appropriate thresholds, the chip starts. The reference block starts first, generating stable reference voltage and currents, and then the internal regulator is enabled. The regulator provides stable supply for the remaining circuitries. Three events can shut down the chip: EN low, VIN low and thermal shutdown. In the shutdown procedure, the signaling path is first blocked to avoid any fault triggering. The comp voltage and the internal supply rail are then pulled down. The floating driver is not subject to this shutdown command.

### ● Overcurrent and Short Circuit Protection

The DP31263A has cycle-by-cycle over current limit when the inductor current peak value exceeds the set current limit threshold. Meanwhile, output voltage starts to drop until FB is below the Under-Voltage (UV) threshold. When the output is shorted to the ground, the switching frequency is Hiccup mode and the current limit is reduced to lower the short circuit current. The frequency Hiccup helps prevent inductor current runaway and thermal issue during short circuit. The DP31263A exits the hiccup mode once the over current condition is removed.

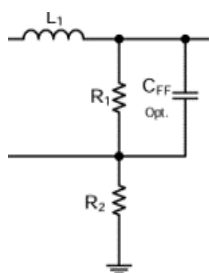
### APPLICATION INFORMATION

The output stage of Asynchronous buck converter is mainly composed of inductor and capacitors. By switching the internally integrated High Side power MOSFET, the energy is stored and transferred to the load, and the second-order LC filter is formed to smooth the switching node voltage so that the stable output DC voltage is obtained.

#### ● Setting Output Voltage

The output voltage is set by FB voltage, which is divided by resistor (R1 & R2) from output node to Ground. That resistor with 1% or higher accuracy is preferred. The output voltage value is set by equation as below.

$$V_{OUT} = V_{FB} \times ((R1 + R2)/R2)$$



Vref is the internal reference voltage of DP31263A, 0.8V.

voltage. The common value of the inductance is between 22uH to 33uH. A larger value inductor will result in less current ripple and lower output voltage ripple. However, the larger value inductor will have larger physical size, higher DC resistance, and/or lower saturation current. A good rule to calculate the inductance is to allow the peak-to-peak ripple current in the inductor to be approximately 30% of the maximum load current. At the same time, it is needed to make sure that the peak inductor current is below the inductor saturation current.

The inductance value can be calculated by:

$$L = \frac{V_{OUT}}{f_s \times \Delta I_L} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right)$$

Where VOUT is the output voltage, VIN is the input voltage, fs is the switching frequency, and ΔL is the peak-to-peak inductor ripple current.

The maximum inductor peak current is:

$$I_{L(MAX)} = I_{LOAD} + \frac{\Delta I_L}{2}$$

The choice of which style inductor to use mainly depends on the price vs. size requirements and any EMI constraints.

Under light load conditions below 100mA, larger inductance is recommended for improved efficiency

#### ● Input capacitors selection

The input current to the step-down converter is discontinuous, therefore a capacitor is required to supply the AC current to the converter. It is recommend to use low ESR capacitors to optimize the performance. Ceramic capacitor is preferred, but tantalum or low-ESR electrolytic capacitors may also meet the requirements. It is better to choose X5R or X7R dielectrics when using ceramic capacitors.

Since the input capacitor (CIN) absorbs the input switching current, a good ripple current rating is required for the capacitor. The RMS current in the input capacitor can be estimated by:

**Table1 Recommend Component Selection Table**

VOUT (V)	R1 (kΩ)	R2 (kΩ)	BS (uF)	D1	L1 (uH)	CIN (uF)	COUT (uF)	CFF (pF) Opt.
5	10.5	2	0.1	SS5 10	22	22	44	Opt.
9	20.5	2	0.1	SS5 10	22	22	44	Opt.
12	28	2	0.1	SS5 10	22	22	44	Opt.

#### ● Inductor selection

An inductor is required to supply constant current to the load while being driven by the switched input

$$I_{CIN} = I_{load} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)}$$

The worst-case condition occurs at  $V_{IN} = 2 \times V_{OUT}$ , where:

$$I_{CIN} = \frac{I_{load}}{2}$$

For simplification, choose the input capacitor whose RMS current rating is greater than half of the maximum load current. When electrolytic or tantalum capacitors are used, a small, high quality ceramic capacitor, i.e. 0.1μF, should be placed as close to the IC as possible. When ceramic capacitors are used, make sure that they have enough capacitance to maintain voltage ripple at input. The input voltage ripple caused by capacitance can be estimated by:

$$\Delta V_{IN} = \frac{I_{load}}{f_s \times C_{IN}} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$

$C_{IN}$  is the input capacitance.

#### ● Output capacitors selection

The output capacitor ( $C_{OUT}$ ) is required to maintain the DC output voltage. Ceramic, tantalum, or low ESR electrolytic capacitors are recommended. Low ESR capacitors are preferred to keep the output voltage ripple low. The output voltage ripple can be estimated by:

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_s \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times \left(R_{ESR} + \frac{1}{8 \times f_s \times C_{OUT}}\right)$$

Where  $L$  is the inductor value,  $R_{ESR}$  is the equivalent series resistance (ESR) value of the output capacitor and  $C_{OUT}$  is the output capacitance value. In the case of ceramic capacitors, the impedance at the switching frequency is dominated by the capacitance. The output voltage ripple is mainly determined by the capacitance. For simplification, the output voltage ripple can be estimated by:

$$\Delta V_{OUT} = \frac{V_{OUT}}{8 \times f_s^2 \times L \times C_{OUT}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$

In the case of tantalum or electrolytic capacitors, the ESR dominates the impedance at the switching frequency. For simplification, the output ripple can be approximated to:

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_s \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times R_{ESR}$$

The characteristics of the output capacitor also affect the stability of the regulation system. The DP31212S/FS can be optimized for a wide range of capacitance and ESR values.

#### ● Feed-Forward Capacitor Selector(CFF)

DP31263A has internal loop compensation, so adding CFF is optional. Specifically, consider whether to add feed-forward capacitors according to the situation.

The use of a feed-forward capacitor (CFF) in the feedback network is to improve the transient response or higher phase margin. To reduce transient ripple, the feed-forward capacitor value can be increased to push the cross frequency to higher region. Although this can improve transient response, it also decreases phase margin and cause more ringing. In the other hand, if more phase margin is desired, the feed-forward capacitor value can be decreased to push the cross frequency to lower region.

the value of feed-forward capacitor (CFF) can be calculated with the following equation:

$$C_{ff\_op} = \frac{1}{2\pi \times f_{\_nocff}} \times \sqrt{\frac{1}{R_1} \times \left(\frac{1}{R_1} + \frac{1}{R_2}\right)}$$

Where  $F_{\_nocff}$  is the cross frequency. the crossing frequency is generally taken as 1/10 to 1/5 of the switching frequency,  $R_1$  and  $R_2$  are feedback resistors.

#### ● Bootstrap Capacitor Selection



The recommended capacitor is 0.1  $\mu$ F and rated 16 V or higher. The bootstrap capacitor is located between the SW pin and the BOOT pin. The bootstrap capacitor must be a high-quality ceramic type with an X7R or X5R grade dielectric for temperature stability.

### ● Schottky Diode Selection

The breakdown voltage rating of the diode is preferred to be 25% higher than the maximum input voltage. The current rating for the diode must be equal to the maximum output current for best reliability in most applications. In cases where the input voltage is much greater than the output voltage, the average diode current is lower. In this case it is possible to use a diode with a lower average current rating, approximately  $(1-D) \times I_{OUT}$  however the peak current rating must be higher than the maximum load current. A 3-A rated diode is a good starting point.

### ● Switching Frequency

For desired frequency, use to calculate the required value for RT.

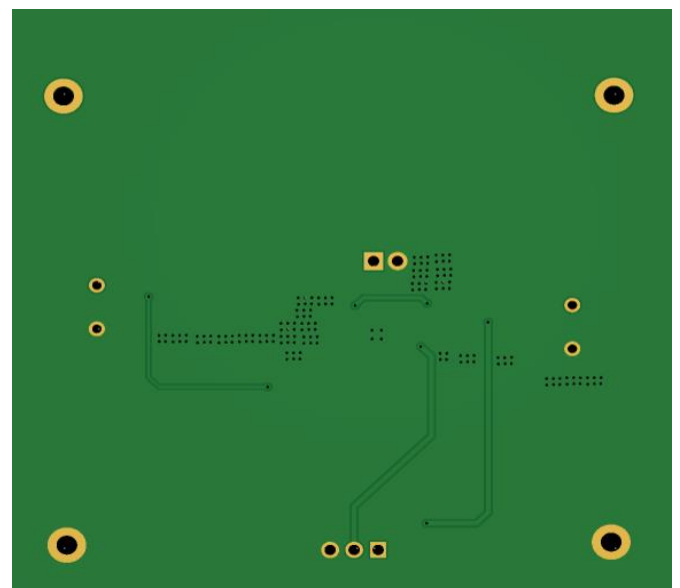
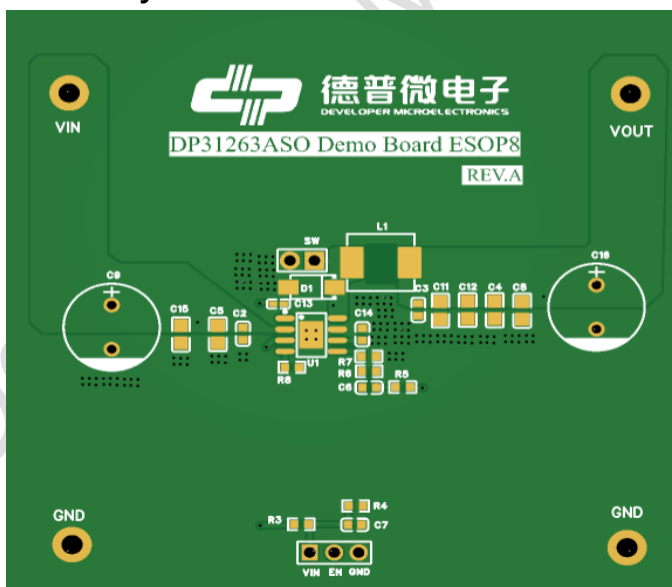
$$RT (K\Omega) = 173000 \cdot F_{SW} (KHz)^{-1.083}$$

For 500 KHz, the calculated RT is 206.5 k $\Omega$  and standard value 200 k $\Omega$  can be used to set the switching frequency at 500 KHz.

### ● PCB Layout

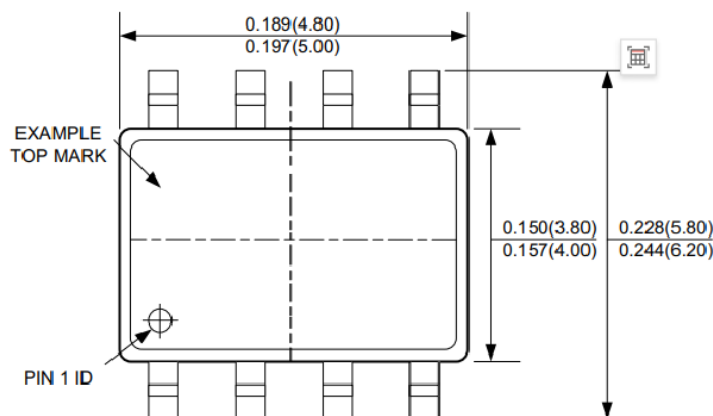
PCB layout is a critical portion of good power supply design. The following guidelines will help users design a PCB with the best power conversion efficiency, thermal performance, and minimized EMI.

1. The feedback network, resistor R7 and R8, should be kept close to FB pin. Vout sense path should stay away from noisy nodes, such as SW & BS signals and preferably through a layer on the other side of shielding layer.
2. The input bypass capacitor C5 and C2 must be placed as close as possible to the VIN pin and ground. Grounding for both the input and output capacitors should consist of localized top side planes that connect to the GND pin and PAD. It is a good practice to place a ceramic cap near the VIN pin to reduce the high frequency injection current.
3. The inductor L should be placed close to the SW pin to reduce magnetic and electrostatic noise.
4. The output capacitor, COUT should be placed close to the junction of L and the diode D. The L, D, and COUT trace should be as short as possible to reduce conducted and radiated noise and increase overall efficiency.
5. The ground connection for C5, C2, C15, C9 and C8, C4, C3, C12 should be as small as possible and connect to system ground plane at only one spot (preferably at the COUT ground point) to minimize injecting noise into system ground plane.
6. Large GND Copper Pour near IC is recommended to minimize the heat of IC.

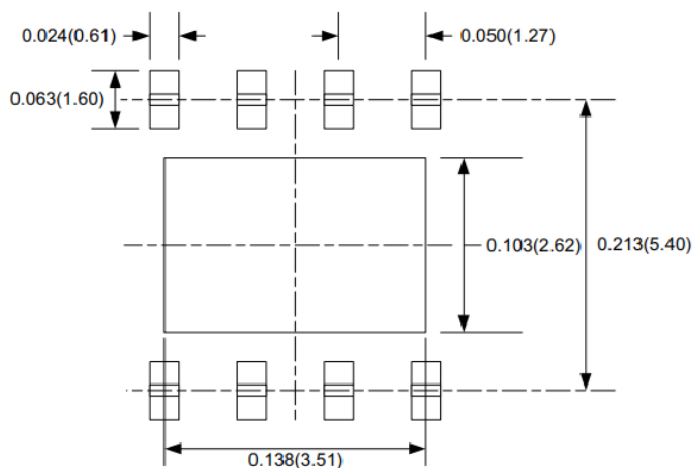


## PACKAGE DIMENSION

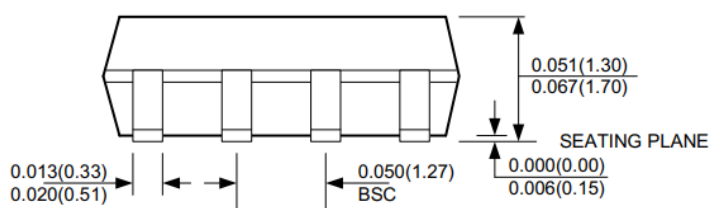
**ESOP8 (EXPOSED PAD)**



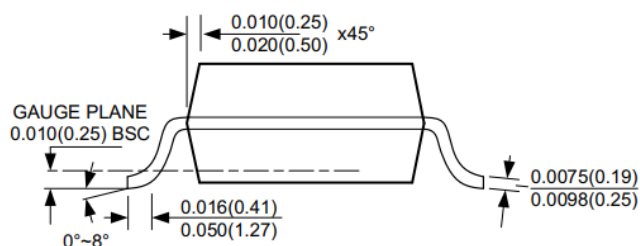
### TOP VIEW



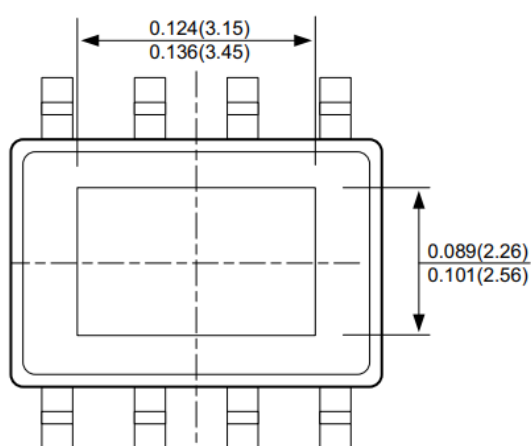
## RECOMMENDED PAD LAYOUT



**FRONT VIEW**



### SIDE VIEW



### BOTTOM VIEW

**NOTE:**

1. CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
2. PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
3. PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
4. LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
5. DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.
6. DRAWING IS NOT TO SCALE.

**REVISION HISTORY**

Editions	Revised Date	Redaction person	Revision content
A.0	2023/12/23	PXB	First release

## OFFICIAL ANNOUNCEMENT

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Division I has been committed to improving the quality and reliability of products, but all semiconductor products have a certain probability of failure, which may lead to some personal accidents, fire accidents, etc. When designing products, pay full attention to redundancy design and adopt safety indicators, so as to avoid accidents.

When using our chips to produce products, Division I shall not be liable for any patent dispute arising from the use of the chip in the product, the specification of the product, or the country of import, etc., in the event of a patent dispute over the products including the chip.